Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A ~~Method~~ method for producing an irreversible storage medium ~~comprising~~ including an array of memory cells, each memory cell ~~comprising~~ including one zone of an active layer arranged between first and second conductors, binary information stored in ~~the~~ each memory cell being determined by the electrical conducting state ~~of the~~ of a corresponding zone, the method comprising:

~~assembly of~~ assembling a blank storage medium having ~~an active layer~~ the active layer, which is in an initial insulating ~~state,~~ state;

~~production of~~ producing a stamping die having a stamping pattern that corresponds to the binary information to be ~~stored,~~ stored; and

stamping ~~of~~ the storage medium using the stamping die so as to make predetermined zones of the active layer electrically conductive by means of localised plastic deformation.

2. (Currently Amended) The ~~Method~~ method according to claim 1, wherein the active layer is formed by a charged resin.

3. (Currently Amended) The ~~Method~~ method according to claim 1, wherein ~~assembly of a~~ the assembling the blank storage medium successively ~~comprises~~ includes:

[-] ~~deposition,~~ depositing on a ~~substrate, of~~ substrate, a first conducting layer and ~~of~~ two oppositely doped semi-conducting ~~layers,~~ layers;

[-] etching ~~of the~~ a stack formed by the first conducting layer and the two semi-conducting layers so as to obtain a first array of parallel ~~strips,~~ strips;

[-] filling ~~the~~ a space between the strips of the first array of parallel strips so as to create a common plane with the strips of the first array of parallel ~~strips,~~ strips;

[-] ~~deposition of~~ depositing the active layer on ~~said~~ the common ~~plane;~~ plane;

[-] ~~deposition of~~ depositing a second conducting layer on the active ~~layer;~~ layer;

etching ~~of~~ the second conducting ~~layer,~~ layer so as to obtain a second array of parallel strips perpendicular to the strips of the first array of ~~strips,~~ strips; and

filling the space between the strips of the second array of parallel strips.

4. (Currently Amended) The ~~Method~~ method according to claim 3, wherein the space between the strips of the first and/or second array of parallel strips is filled by means of a technique using a planarization resin.

5. (Currently Amended) The ~~Method~~ method according to claim 3, wherein the space between the strips of the first and/or second array of parallel strips is filled by means of a mechanical-chemical polishing step.

6. (Currently Amended) The ~~Method~~ method according to claim 1, wherein ~~production of~~ the producing the stamping die successively ~~comprises~~ includes:

[-] ~~deposition of~~ depositing a photoresist on an intermediate ~~substrate;~~ substrate;

[-] ~~etching;~~ etching in the ~~photoresist, of~~ photoresist, an array of elementary zones having a configuration corresponding to the stamping ~~pattern;~~ pattern;

[-] ~~electrolytic deposition,~~ electrolytically depositing on the intermediate substrate and the ~~photoresist, of~~ photoresist a metal constituting the stamping ~~die;~~ die;

[-] ~~detachment of~~ detaching the stamping die from the intermediate ~~substrate;~~ subtrate; and

[-] ~~removal of~~ removing the residues of the photoresist from the stamping die.

7. (Currently Amended) An ~~Irreversible~~ irreversible storage ~~medium,~~ mediumobtained by means of a formed by the method according to claim 1.